

NP160N055TUK

MOS FIELD EFFECT TRANSISTOR

R07DS0592EJ0100 Rev.1.00 Dec 12, 2011

Description

The NP160N055TUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

• Super low on-state resistance

 $R_{DS(on)} = 2.10 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, I_D = 80 \text{ A})$

- Low C_{iss} : $C_{iss} = 7500 \text{ pF TYP.} (V_{DS} = 25 \text{ V})$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Pac	Package	
NP160N055TUK-E1-AY *1	Pure Sn (Tin)	Tape 800 p/reel	Taping (E1 type)	TO-263-7pin
NP160N055TUK-E2-AY *1			Taping (E2 type)	(MP-25ZT)

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	55	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±160	Α
Drain Current (pulse) *1	I _{D(pulse)}	±640	Α
Total Power Dissipation (T _C = 25°C)	P _{T1}	250	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to 175	°C
Repetitive Avalanche Current *2	I _{AR}	51	А
Repetitive Avalanche Energy *2	E _{AR}	260	mJ

Notes: *1 $\,T_{C}$ = 25°C, $P_{W} \leq$ 10 $\mu s, \, Duty \, Cycle \leq$ 1%

Thermal Resistance

^{*2} $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 V$

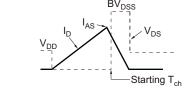
Electrical Characteristics (T_A = 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 55 \text{ V}, V_{GS} = 0 \text{ V}$	
Gate Leakage Current	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Forward Transfer Admittance *1	y _{fs}	60	120	_	S	$V_{DS} = 5 \text{ V}, I_{D} = 80 \text{ A}$	
Drain to Source On-state Resistance *1	R _{DS(on)}	_	1.75	2.10	mΩ	$V_{GS} = 10 \text{ V}, I_{D} = 80 \text{ A}$	
Input Capacitance	C _{iss}	_	7500	11250	pF	V _{DS} = 25 V	
Output Capacitance	Coss	_	770	1160	pF	$V_{GS} = 0 V$	
Reverse Transfer Capacitance	C _{rss}	_	270	490	pF	f = 1 MHz	
Turn-on Delay Time	t _{d(on)}	_	30	70	ns	$V_{DD} = 28 \text{ V}, I_D = 80 \text{ A}$	
Rise Time	t _r	_	14	40	ns	V _{GS} = 10 V	
Turn-off Delay Time	t _{d(off)}	_	100	200	ns	$R_G = 0 \Omega$	
Fall Time	t _f	_	11	30	ns		
Total Gate Charge	Q_G	_	126	189	nC	V _{DD} = 44 V	
Gate to Source Charge	Q_{GS}	_	32	_	nC	$V_{GS} = 10 \text{ V}$	
Gate to Drain Charge	Q_{GD}	_	31	_	nC	I _D = 160 A	
Body Diode Forward Voltage *1	$V_{F(S-D)}$	_	0.9	1.5	V	I _F = 160 A, V _{GS} = 0 V	
Reverse Recovery Time	t _{rr}	_	62	_	ns	I _F = 160 A, V _{GS} = 0 V	
Reverse Recovery Charge	Q _{rr}	_	135		nC	di/dt = 100 A/μs	

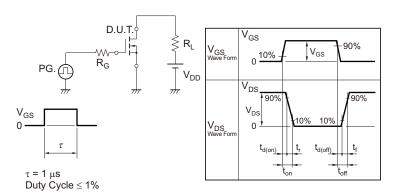
Note: *1 Pulsed test

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DS} V_{DS}



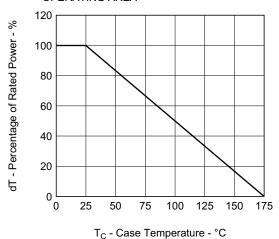
TEST CIRCUIT 2 SWITCHING TIME



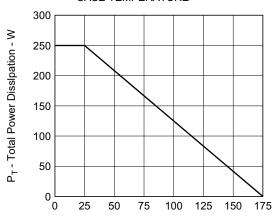
TEST CIRCUIT 3 GATE CHARGE

Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

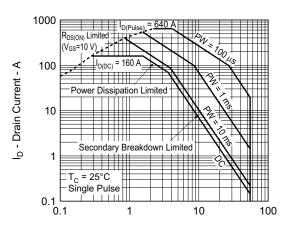


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



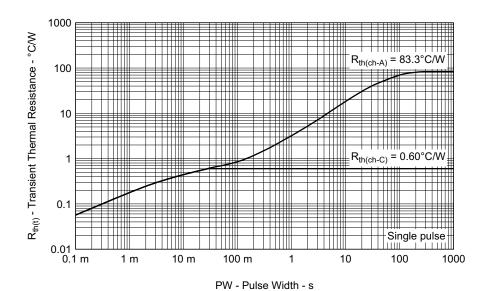
T_C - Case Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



 V_{DS} - Drain to Source Voltage - V

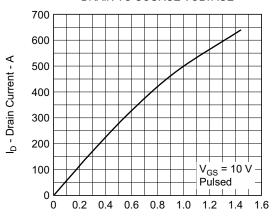
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



V_{GS(th)} - Gate to Source Threshold Voltage - V

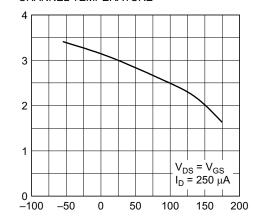
 $R_{DS(on)}$ - Drain to Source On-State Resistance - $m\Omega$

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



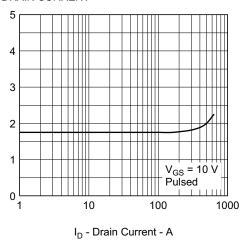
V_{DS} - Drain to Source Voltage - V

GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

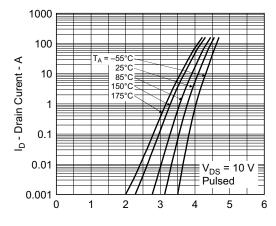


T_{ch} - Channel Temperature - °C

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

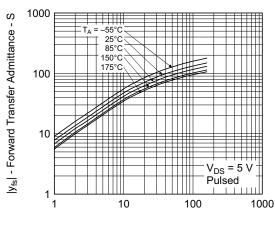


FORWARD TRANSFER CHARACTERISTICS



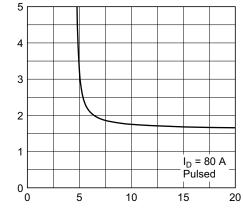
V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

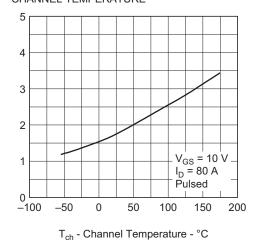


V_{GS} - Gate to Source Voltage - V

 $R_{\text{DS(on)}}$ - Drain to Source On-State Resistance - $m\Omega$

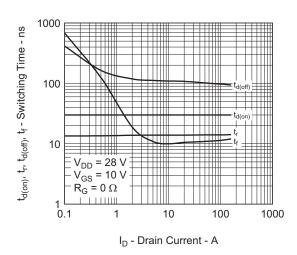
 $R_{DS(on)}$ - Drain to Source On-State Resistance - $m\Omega$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

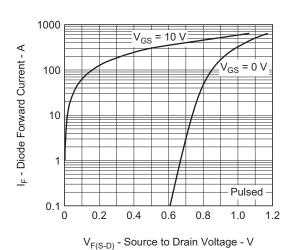


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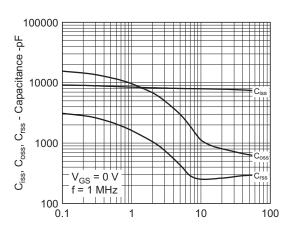
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

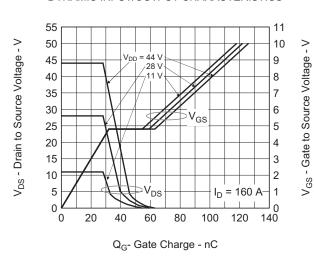


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

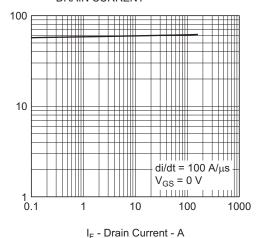


V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



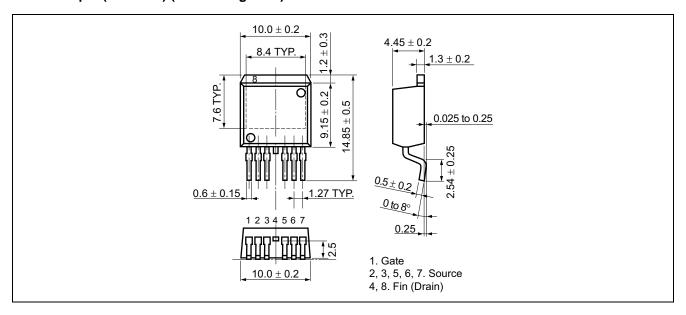
REVERSE RECOVERY TIME vs. DRAIN CURRENT



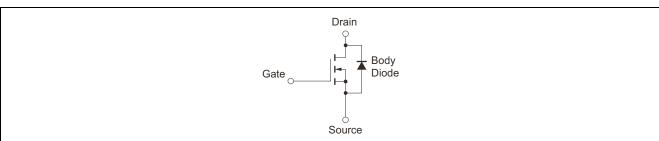
t_{rr} - Reverse Recovery Time - ns

Package Drawing (Unit: mm)

TO-263-7pin (MP-25ZT) (Mass: 1.5 g TYP.)



Equivalent Circuit



Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History

NP160N055TUK Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Dec 12, 2011	_	First Edition Issued	

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